AMENDMENTS

In the Specification:

Amend the Title to read <u>METHOD OF MANUFACTURING</u> INSULATED GATE SEMICONDUCTOR DEVICE <u>AND MANUFACTURING METHOD THEREOF</u>.

On the first page, after the Title, insert as the first paragraph of the specification the following new paragraph.

Reference to Related Applications:

•	This application is	a division	of Serial No.	. 09/925,	628, file	d August	10, 20	001, now	U.S.
Patent	No.				•				